規格承認書

文件編號 ：

客戶名稱 ：

客户料号：

翱龙料号 ： AL205

送樣日期 ：

簽程:	
工程:	胡瑞明
品管:	王德力
日期:	2019-11-12

客戶確認簽程:	
工程:	
品管:	
日期:	

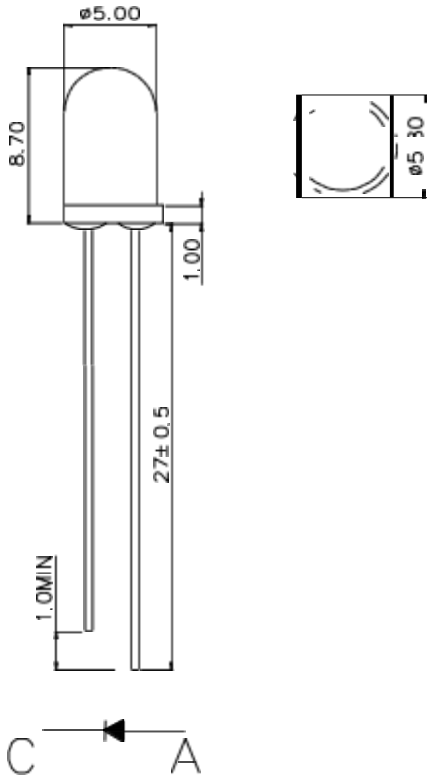
上海翱龙电子科技有限公司
Shanghai Along Electronic Technology Co.,Ltd
联系电话：13776267687(微信同号）
网址:www.along-china.com

INFRARED EMITTING DIODE AL205

Features

- High radiant power and high radiant intensity
- Suitable ror DC and high pulse current operation
- Standard T-1 3/4 (ϕ 5mm) package, radiation angle: 40°
- Peak wavelength λp = 940 nm
- Good spectral matching to si-photodetector

Package Dimensions



Notes：

1、All dimensions are in millimeters

2. Tolerance is ± 0.3 mm unless otherwise noted.

3. Protruded resin under flange is 1.5 mm max.

4. Lead spacing is measured where the leads emerge from the package.

Lens	Chip Material
Blue	GaAs /AlGaAs

Absolute Maximum Ratings at T_A=25℃

Parameter	Maximum Rating	Unit
Power Dissipation	150	mW
Peak Forward Current (1/10 Duty Cycle, 0.1ms Pulse Width)	1	A
Continuous Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55℃ to +100℃	
Storage Temperature Range	-55℃ to +100℃	
Lead Soldering Temperature(1.6mm From Body)	260℃ for 5 seconds	

Optical-Electrical Characteristics at TA=25℃

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Radiant Intensity	I_F=20mA	Ie		12		mW/sr
Forward Voltage	I_F=20mA	V_F		1.2	1.5	V
Reverse Current	V_R=5V	I_R			100	μA
Peak Wavelength	2010.10.30	λp		940		nm
Spectral Bandwidth	I_F=20mA	Δλ		50		nm
View Angle	I_F=20mA	$2\theta_{1/2}$		40		deg .

Typical Optical-Electrical Characteristic Curves

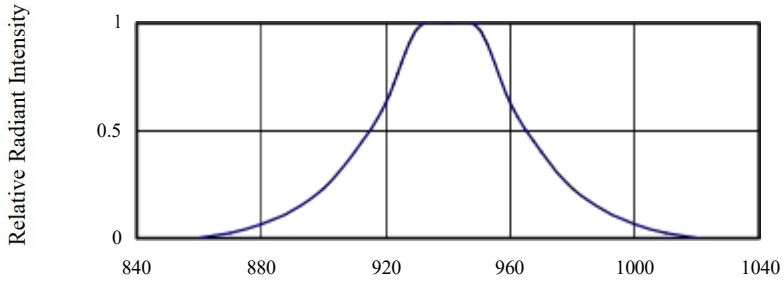


FIG.1 SPECTRAL DISTRIBUTION

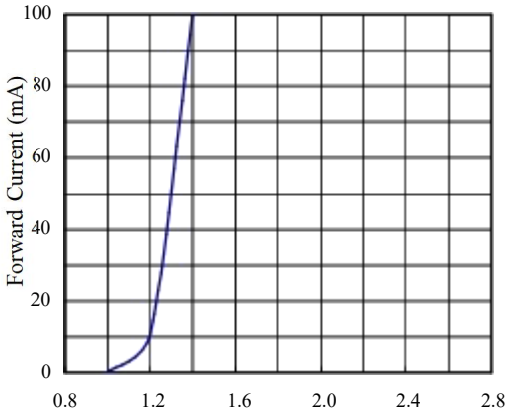


FIG.2 FORWARD CURRENT VS. FORWARD VOLTAGE

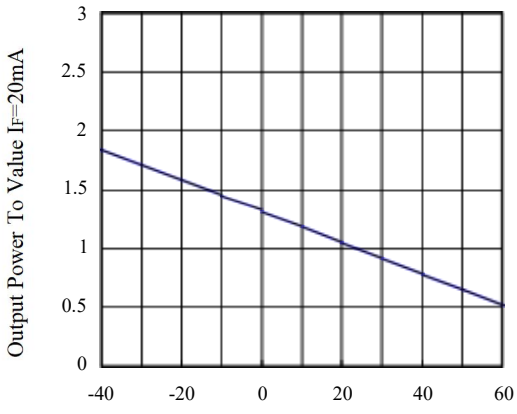


FIG.3 RELATIVE RADIANT INTENSITY VS.AMBIENT TEMPERATURE

2010.10.30

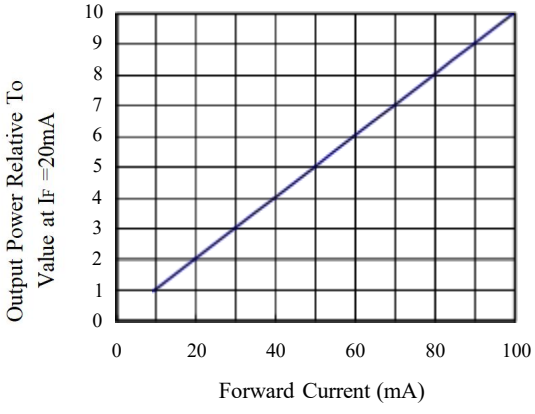


FIG.4 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

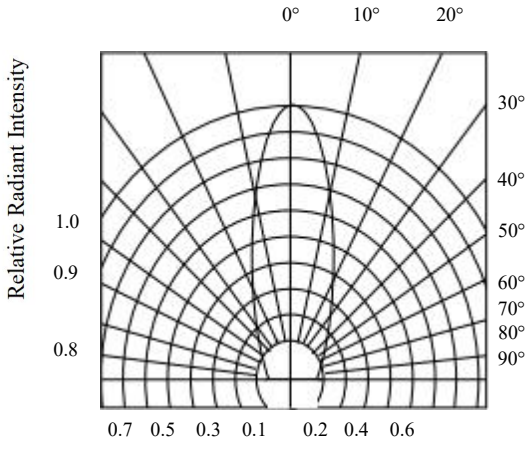


FIG.5 RADIATION DIAGRAM